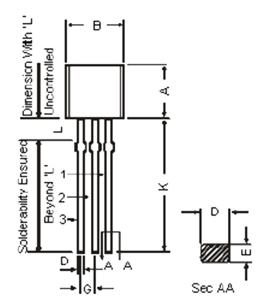


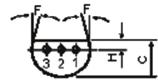


Description:

Silicon Planar Epitaxial Transistors. General Purpose Transistors Best Suited for use in Driver and Output Stages of Audio Amplifier.



Dimensions	Minimum (mm)	Maximum (mm)
A	4.42	5.33
В	4.45	5.20
С	3.18	4.19
D	0.41	0.55
E	0.35	0.50
F	5°	
G	1.14	1.40
Н	1.20	1.53
К	12.70	-
L	1.982	2.082

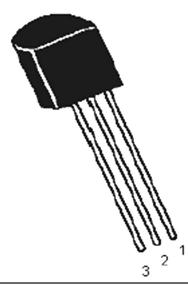


Dimensions : Millimetres

Pin Configuration:

- 1. Emitter
- 2. Base
- 3. Collector

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Absolute Maximum Ratings (T_a = 25°C unless specified otherwise)

Description	Symbol	Value	Unit
Collector Emitter Voltage	Vceo	45	V
Collector Emitter Voltage	Vces	50	
Emitter Base Voltage	Vево	5	
Collector Current Continuous	lc	800	mA
Collector Current Peak	Ісм	1000	
Base Current Peak	Івм	200	
Base Current Continuous	Ів	100	
Base Current Peak	Івм	200	
Power Dissipation at Ta = 25°C Derate Above 25°C	Po	625 5	mW mW/°C
Operating and Storage Junction Temperature Range	T _j , T _{stg}	-65 to +150	°C
Thermal Resistance		^	•
Junction to Ambient in Free Air	R _{th (j-a)}	200	°C/W

Electrical Characteristics (T_a = 25°C unless specified otherwise)

Description	Symbol	Test Condition	Minimum	Maximum	Unit
Collector Emiiter Voltage	Vceo	lc = 1mA, I _R = 0	45	-	
Collector Emiiter Voltage	Vces	Ic = 100μΑ, Iε = 0	50	-	V
Emitter Base Voltage	Vebo	Iε = 10μΑ, Ic = 0	5.0	-	
Collector Cut off Current	Ісво	V _{CB} = 20V, I _E = 0 V _{CB} = 20V, I _E = 0, T _j = 150°C	-	100 5	nA µA
Emitter Cut off Current	Іево	VEB = 5V, IC = 0	-	10	μA
Collector Emitter Saturation Voltage	*VCE (sat)	Ic = 500mA, Iв = 50mA	-	0.7	V
Base Emitter On Voltage	*VBE (on)	Ic = 500mA, Vce = 1V	-	1.2	V

*Pulse Test: Pulse Width ≤300ms, Duty Cycle ≤2%.

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Electrical Characteristics ($T_a = 25^{\circ}C$ unless specified otherwise)

Description	Symbol	Test Condition	Minimum	Typical	Maximum	Unit
DC Current Gain	hfe	IC = 100mA, VCE = 1V	100	400	-	-
Small Signal Characteristics						
Transistors Frequency	fτ	IC = 10mA, VCE = 5V, f = 35MHz PNP	-	100	-	MHz
Input Capacitance	C _{ib}	VBE = 10V, IE = 0, f = 1MHz PNP	-	8	-	pF

Specifications

Vсео (V)	Vсво Maximum (V)	lc (A)	hғe Minimum at Ic = 2mA	f⊤ Minimum (MHz)	P _{tot} (mW)	Package
45	50	0.8	100	60	625	TO-92

Part Number Table

Description	Part Number	
Bipolar Transistor, PNP, -45V TO-92	BC327.25	

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